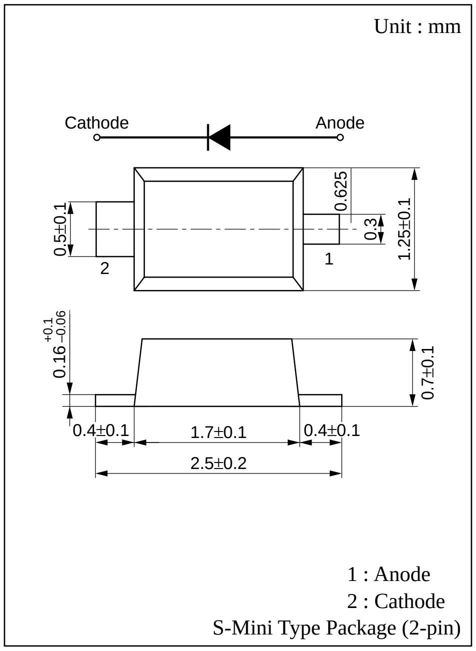
MA112

Silicon epitaxial planer type

For switching circuits



Marking Symbol : 1C

■ Features

- ● Small S-Mini type package enabling high density mounting
- ● Securing of the current capacity of the forward current (average) $I_{F(AV)}$= 200mA

■ Absolute Maximum Ratings (Ta= 25˚C)

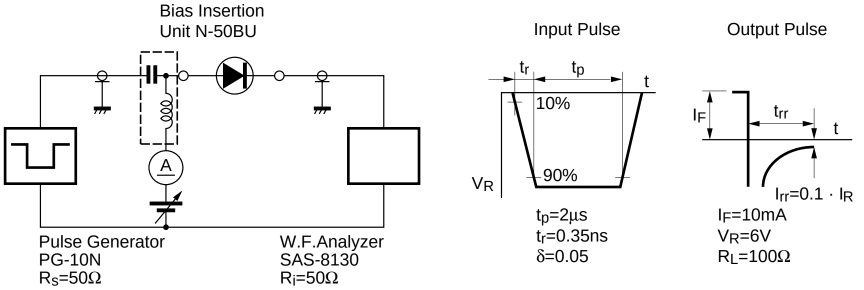
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Peak reverse voltage	V_{RM}	40	V
Average forward current	$I_{F\ (AV)}$*[1]	200	mA
Peak forward current	I_{FM}	600	mA
Non-repetitive peak forward surge current	I_{FSM} *[2]	1	mA
Junction temperature	T_j	150	˚C
Storage temperature	T_{stg}	– 55 to +150	˚C

*[1] With a printed-circuit board
*[2] t=1s

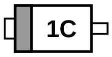
■ Electrical Characteristics (Ta= 25˚C)

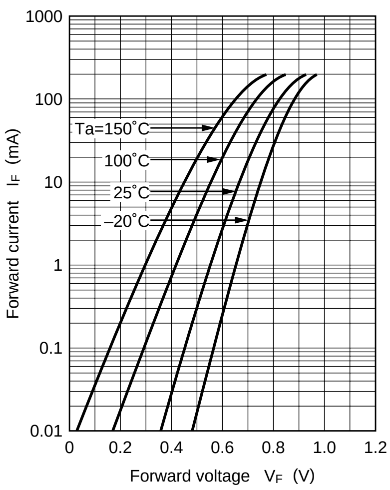
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_{R1}	V_R=15V			50	nA
	I_{R2}	V_R= 35V			500	nA
	I_{R3}	V_R= 35V, Ta=100˚C			500	µA
Forward voltage (DC)	V_F	I_F= 200mA			1.1	V
Terminal capacitance	C_t	V_R= 0V, f=1MHz			4	pF
Reverse recovery time	t_{rr} *	I_F=10mA, V_R= 6V I_{rr}= 0.1 · I_R, R_L=100Ω			10	ns

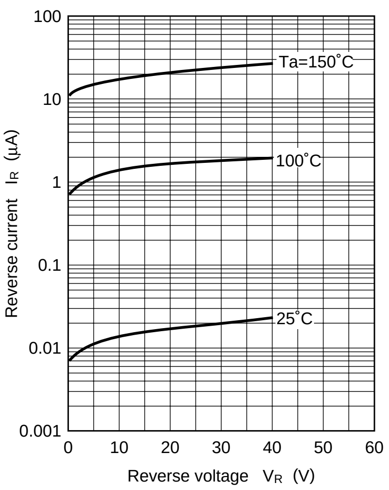
Note 1. Rated input/output frequency : 100MHz
2. ∗ : t_{rr} measuring circuit

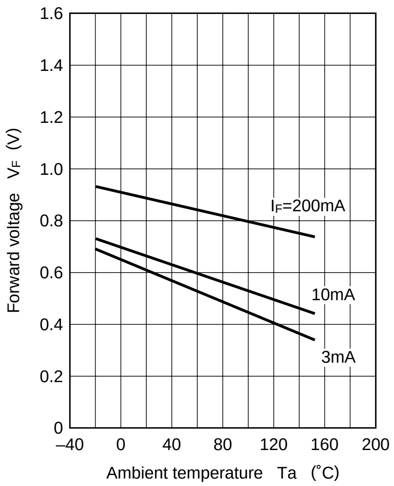


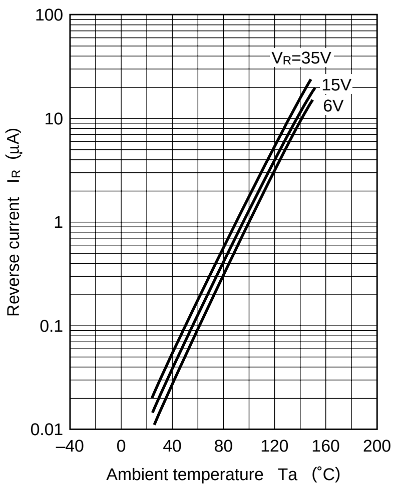
■ Marking

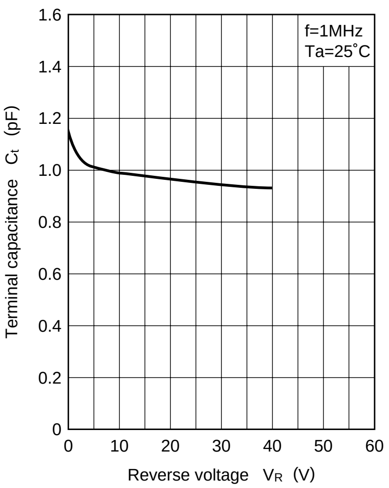


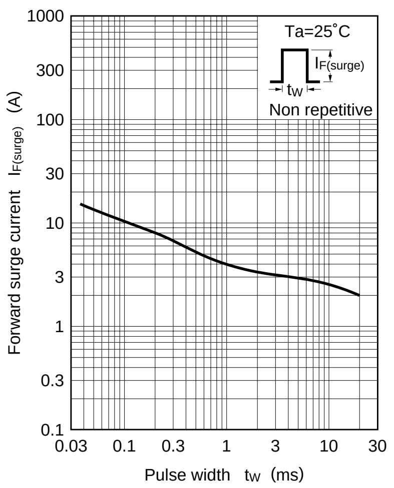

$I_F – V_F$


$I_R – V_R$


$V_F – Ta$


$I_R – Ta$


$C_t – V_R$


$I_{F\ (surge)} – t_W$